

Serial No.

**INFORMATION DISCLOSURE  
CITATION**

**160-386**

**10/609,410**

**Applicant**

**NAKAMURA et al.**

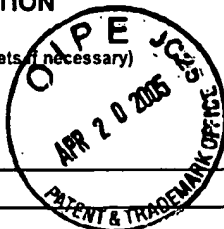
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## U.S. PATENT DOCUMENTS

[illegible]

## FOREIGN PATENT DOCUMENTS

[illegible]

**OTHER DOCUMENTS (including Author, Title, Date, Pertinent pages, etc.)**

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**\*Examiner**

V- Yugra

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## U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
VY	5,369,289	11/1994	Tamaki			
	5,247,533	9/1993	Okazaki et al			
	4,495,514	1/1985	Lawrence et al			
	5,281,830	1/1994	Kotaki et al			
	4,153,905	5/1979	Charmakadze et al			
VY	5,285,078	2/1994	Mimura et al			

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DOCUMENT	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO
VY 03-218625	9/1991	Japan			abs
05-013812	1/1993	Japan			abs
51-85384	7/1976	Japan			abs
56-81986	7/1981	Japan			abs
61-144859	9/1986	Japan			abs
63-61161	4/1988	Japan			abs
61-87381	5/1986	Japan			abs
02-229475	9/1990	Japan			abs
59228776	12/1984	Japan			abs
55009442 A	1/1980	Japan			abs
1990-0701577	7/1990	Korea			abs
5-211347	8/1993	Japan			abs
3-183173	8/1991	Japan			abs
4-68579	3/1992	Japan			abs
5-129658	5/1993	Japan			abs
57-111076	7/1982	Japan			abs
5-13816	1/1993	Japan			abs
62-2675	1/1987	Japan			X
62-287675	12/1987	Japan			abs
83103775	4/1994	Taiwan			X
7-45867	2/1995	Japan			abs
5-291621	11/1993	Japan			abs
5-129658	5/93	Japan			abs
0 483 688 A3	5/92	Europe			
0 483 688 A2	5/92	Europe			
VY 57-45272	3/82	Japan			abs

\*Examiner

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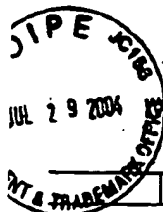
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YES NO

✓	6-38265	5/94	Japan	—	Abs	
✓	62-101090	5/87	Japan	—	Abs	
✓	10-0225612	7/99	Korea	—	Abs	
✓	2-68968	3/90	Japan	—	Abs	

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✓	Oyo Buturi Vol. 60, No. 2, 1991 02; p. 164
✓	Hayes et al Proceedings of Symposium B 1990 Extended Abstracts EA-21 Electronic Optical and Device Properties of Layered Structures
	Amano et al Japanese Journal of Applied Physics Vol. 28 No. 12, 1989 L2112-L2114 P-Type Conduction in Mg-Doped GaN Treated with Low-Energy Electron Beam Irradiation (LEEBI)
	Nakamura et al Jpn J. Appl. Phys. Vol. 31 (1992) pp 1258-1266 Hole Compensation Mechanisms of P-Type GaN Films Dept. Of Electrical Engineering
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	Foresi et al "Metal contacts to gallium nitride" Appl. Phys. Letts 62 (1993 31 May No. 22, pp. 2859-2861
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	Nakamura et al "High-power InGaN/GaN..." Appl. Phys. Letts. 62 (19) 10 May 1993 pp 2390-2392
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✓	Database WPI, Week 9438, Derwent Publications Ltd. London GV An 94-308360 & JP A 6 237 012 (Nichia Kagaku Kogyo KK) 23 Au. 1994, see abstract

\*Examiner

V. J. Johnson

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10/292,583

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VU	5,285,078	2/1994	Mimura et al			

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